Noninverting 3-State Buffer

MC74VHC1G125. MC74VHC1GT125

The MC74VHC1G125 / MC74VHC1GT125 is a single non-inverting 3-state buffer in tiny footprint packages. The MC74VHC1G125 has CMOS-level input thresholds while the MC74VHC1GT125 has TTL-level input thresholds.

The internal circuit is composed of three stages, including a buffered 3-state output which provides high noise immunity and stable output.

The input structures provide protection when voltages up to 5.5 V are applied, regardless of the supply voltage. This allows the device to be used to interface 5 V circuits to 3 V circuits. The output structures also provide protection when $V_{CC} = 0$ V and when the output voltage exceeds V_{CC}. These input and output structures help prevent device destruction caused by supply voltage - input/output voltage mismatch, battery backup, hot insertion, etc.

Features

- Designed for 2.0 V to 5.5 V V_{CC} Operation
- 3.5 ns t_{PD} at 5 V (typ)
- Inputs/Outputs Over-Voltage Tolerant up to 5.5 V
- IOFF Supports Partial Power Down Protection
- Source/Sink 8 mA at 3.0 V
- Available in SC-88A, SC-74A, TSOP-5, SOT-553, SOT-953 and **UDFN6** Packages
- Chip Complexity < 100 FETs
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

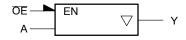
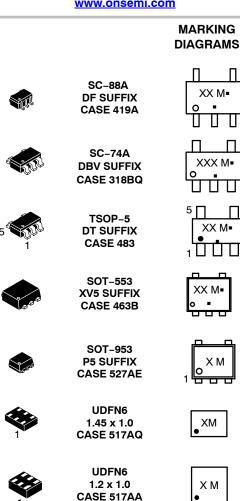


Figure 1. Logic Symbol



ON Semiconductor®

www.onsemi.com



= Specific Device Code = Date Code*

= Pb-Free Package (Note: Microdot may be in either location)

XX

UDFN6 1.0 x 1.0

CASE 517BX

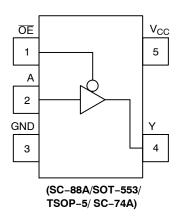
*Date Code orientation and/or position may vary depending upon manufacturing location.

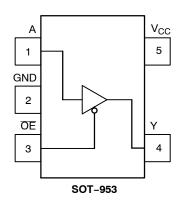
ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 9 of this data sheet

XM

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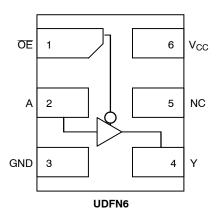


Figure 2. Pinout (Top View)

(SC-88A/SOT-553/ TSOP-5/SC-74A)

PIN ASSIGNMENT

Pin	Function
1	ŌĒ
2	Α
3	GND
4	Y
5	V _{CC}

PIN ASSIGNMENT (SOT-953)

Pin	Function
1	А
2	GND
3	ŌĒ
4	Y
5	V _{CC}

PIN ASSIGNMENT (UDFN)

Pin	Function
1	ŌĒ
2	А
3	GND
4	Y
5	NC
6	V _{CC}

FUNCTION TABLE

Inp	Output	
ŌĒ	Α	Υ
L	L	L
L	Н	Н
Н	Х	Z

X = Don't Care

MAXIMUM RATINGS

Symbol	Characteristics		Value	Unit
V _{CC}	DC Supply Voltage TSOP-5, S SC-74A, SC-88A, UDFN6, SOT-5	SC-88A (NLV) 553, SOT-953	-0.5 to +7.0 -0.5 to +6.5	V
V_{IN}	DC Input Voltage TSOP-5, S SC-74A, SC-88A, UDFN6, SOT-5	SC-88A (NLV) 553, SOT-953	-0.5 to +7.0 -0.5 to +6.5	V
V _{OUT}	DC Output Voltage Active-Mode (High TSOP-5, SC-88A (NLV) Tri-State New Power-Down Mode (NLV)	Mode (Note 1)	-0.5 to V _{CC} + 0.5 -0.5 to +7.0 -0.5 to +7.0	V
	DC Output Voltage Active-Mode (High SC-74A, SC-88A, UDFN6, SOT-553, SOT-953 Tri-State Newer-Down Mod	-0.5 to V _{CC} + 0.5 -0.5 to +6.5 -0.5 to +6.5	V	
I _{IK}	DC Input Diode Current	V _{IN} < GND	-20	mA
l _{ok}	DC Output Diode Current	V _{OUT} < GND	-20	mA
l _{out}	DC Output Source/Sink Current		±25	mA
I _{CC} or I _{GND}	DC Supply Current per Supply Pin or Ground Pin		±50	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 10 secs		260	°C
T_J	Junction Temperature Under Bias		+150	°C
$ heta_{\sf JA}$	Thermal Resistance (Note 2)	SC-88A SC-74A SOT-553 SOT-953 UDFN6	377 320 324 254 154	°C/W
P _D	Power Dissipation in Still Air	SC-88A SC-74A SOT-553 SOT-953 UDFN6	332 390 386 491 812	mW
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating Oxygen Ir	ndex: 28 to 34	UL 94 V-0 @ 0.125 in	
V _{ESD}		n Body Model Device Model	2000 1000	٧
I _{Latchup}	Latchup Performance (Note 4)		±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Applicable to devices with outputs that may be tri-stated.

2. Measured with minimum pad spacing on an FR4 board, using 10mm-by-1inch, 2 ounce copper trace no air flow per JESD51-7.

3. HBM tested to ANSI/ESDA/JEDEC JS-001-2017. CDM tested to EIA/JESD22-C101-F. JEDEC recommends that ESD qualification to EIA/JESD22-A115-A (Machine Model) be discontinued per JEDEC/JEP172A.

4. Tested to EIA/JESD78 Class II.

RECOMMENDED OPERATING CONDITIONS

Symbol		Characteristics	Min	Max	Unit
V _{CC}	Positive DC Supply Voltage		2.0	5.5	V
V _{IN}	DC Input Voltage		0	5.5	V
V _{OUT}	DC Output Voltage	TSOP-5, SC-88A (NLV)	0	V _{CC}	V
	DC Output Voltage	SC-74A, SC-88A, UDFN6, SOT-553, SOT-953 Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode ($V_{\rm CC}$ = 0 V)	0 0 0	V _{CC} 5.5 5.5	
T _A	Operating Temperature Ran	ge	-55	+125	°C
t _r , t _f	Input Rise and Fall Time	TSOP-5, SC-88A (NLV) V _{CC} = 3.0 V to 3.6 V V _{CC} = 4.5 V to 5.5 V	0 0	100 20	ns/V
	Input Rise and Fall Time	SC-74A, SC-88A, UDFN6, SOT-553, SOT-953 $V_{CC}=2.0\ V$ $V_{CC}=2.3\ V\ to\ 2.7\ V$ $V_{CC}=3.0\ V\ to\ 3.6\ V$ $V_{CC}=4.5\ V\ to\ 5.5\ V$	0 0 0	20 20 10 5	

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS (MC74VHC1G125)

_		Test	V _{CC}	7	T _A = 25°	С	-40°C ≤	Γ _A ≤ 85°C	-55°C ≤ T	_A ≤ 125°C	
Symbol	Parameter	Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V _{IH}	High-Level Input		2.0	1.5	-	-	1.5	-	1.5	-	V
	Voltage		3.0	2.1	-	-	2.1	-	2.1	-	1
			4.5	3.15	-	-	3.15	-	3.15	-	
			5.5	3.85	-	-	3.85	-	3.85	-	
V _{IL}	Low-Level Input		2.0	-	-	0.5	-	0.5	-	0.5	٧
	Voltage		3.0	-	-	0.9	=	0.9	-	0.9	
			4.5	-	_	1.35	-	1.35	-	1.35]
			5.5	-	-	1.65	_	1.65	-	1.65	
V _{OH}	High-Level Output Voltage	$\begin{aligned} &V_{IN} = V_{IH} \text{ or } V_{IL} \\ &I_{OH} = -50 \mu\text{A} \\ &I_{OH} = -50 \mu\text{A} \\ &I_{OH} = -50 \mu\text{A} \\ &I_{OH} = -4 m\text{A} \\ &I_{OH} = -8 m\text{A} \end{aligned}$	2.0 3.0 4.5 3.0 4.5	1.9 2.9 4.4 2.58 3.94	2.0 3.0 4.5 –	- - - -	1.9 2.9 4.4 2.48 3.80	- - - -	1.9 2.9 4.4 2.34 3.66	- - - -	V
V _{OL}	Low-Level Output Voltage	$\begin{aligned} &V_{IN} = V_{IH} \text{ or } V_{IL} \\ &I_{OL} = 50 \mu\text{A} \\ &I_{OL} = 50 \mu\text{A} \\ &I_{OL} = 50 \mu\text{A} \\ &I_{OL} = 4 \text{ mA} \\ &I_{OL} = 8 \text{ mA} \end{aligned}$	2.0 3.0 4.5 3.0 4.5	- - - -	0.0 0.0 0.0 - -	0.1 0.1 0.1 0.36 0.36	- - - -	0.1 0.1 0.1 0.44 0.44	- - - -	0.1 0.1 0.1 0.52 0.52	V
I _{IN}	Input Leakage Current	V _{IN} = 5.5 V or GND	2.0 to 5.5	-	-	±0.1	-	±1.0	_	±1.0	μΑ
I _{OZ}	3-State Output Leakage Current	V _{OUT} = 0 V to 5.5 V	5.5	-	_	±0.25	-	±2.5	-	± 2.5	μΑ
I _{OFF}	Power Off Leakage Current	V _{IN} = 5.5 V or V _{OUT} = 5.5 V	0	-	-	1.0	-	10	_	10	μΑ
I _{CC}	Quiescent Supply Current	V _{IN} = V _{CC} or GND	5.5	-	-	1.0	-	20	_	40	μΑ

DC ELECTRICAL CHARACTERISTICS (MC74VHC1GT125)

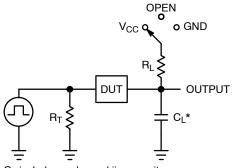
		Test	V _{CC}	7	_ _A = 25°	С	-40°C ≤	Γ _A ≤ 85°C	-55°C ≤ T	T _A ≤ 125°C	
Symbol	Parameter	Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V _{IH}	High-Level Input		2.0	1.0	-	-	1.0	_	1.0	-	٧
	Voltage		3.0	1.4	-	-	1.4	-	1.4	_	1
			4.5	2.0	-	-	2.0	-	2.0	-	1
			5.5	2.0	-	-	2.0	_	2.0	-	
V_{IL}	Low-Level Input		2.0	-	-	0.28	-	0.28	-	0.28	V
	Voltage		3.0	-	-	0.45	=	0.45	-	0.45	
			4.5	-	ı	0.8	-	0.8	-	0.8	
			5.5	-	-	0.8	_	0.8	-	0.8	
V _{OH}	High-Level Output Voltage	$\begin{aligned} &V_{IN} = V_{IH} \text{ or } V_{IL} \\ &I_{OH} = -50 \mu\text{A} \\ &I_{OH} = -50 \mu\text{A} \\ &I_{OH} = -50 \mu\text{A} \\ &I_{OH} = -4 m\text{A} \\ &I_{OH} = -8 m\text{A} \end{aligned}$	2.0 3.0 4.5 3.0 4.5	1.9 2.9 4.4 2.58 3.94	2.0 3.0 4.5 –	- - - -	1.9 2.9 4.4 2.48 3.80	- - - -	1.9 2.9 4.4 2.34 3.66	- - - -	V
V _{OL}	Low-Level Output Voltage	$\begin{aligned} &V_{IN} = V_{IH} \text{ or } V_{IL} \\ &I_{OL} = 50 \mu\text{A} \\ &I_{OL} = 50 \mu\text{A} \\ &I_{OL} = 50 \mu\text{A} \\ &I_{OL} = 4 \text{ mA} \\ &I_{OL} = 8 \text{ mA} \end{aligned}$	2.0 3.0 4.5 3.0 4.5	- - - -	0.0 0.0 0.0 -	0.1 0.1 0.1 0.36 0.36	- - - -	0.1 0.1 0.1 0.44 0.44	- - - -	0.1 0.1 0.1 0.52 0.52	V
I _{IN}	Input Leakage Cur- rent	V _{IN} = 5.5 V or GND	2.0 to 5.5	-	-	±0.1	-	±1.0	_	±1.0	μΑ
I _{OZ}	3-State Output Leakage Current	V _{OUT} = 0 V to 5.5 V	5.5	_	-	±0.25	-	±2.5	_	±2.5	μΑ
I _{OFF}	Power Off Leakage Current	V _{IN} = 5.5 V or V _{OUT} = 5.5 V	0	_	-	1.0	-	10	_	10	μΑ
I _{CC}	Quiescent Supply Current	V _{IN} = V _{CC} or GND	5.5	-	-	1.0	-	20	_	40	μΑ
I _{CCT}	Increase in Quies- cent Supply Current per Input Pin	One Input: V _{IN} = 3.4 V; Other Input at V _{CC} or GND	5.5	-	I	1.35	-	1.5	-	1.65	mA

AC ELECTRICAL CHARACTERISTICS

				T	A = 25°	С	-40°C ≤ 7	Γ _A ≤ 85°C	-55°C ≤ T	A ≤ 125°C	
Symbol	Parameter	Conditions	V _{CC} (V)	Min	Тур	Max	Min	Max	Min	Max	Unit
t _{PLH} ,	Propagation Delay,	C _L = 15 pF	3.0 to 3.6	_	4.5	8.0	-	9.5	_	12.0	ns
t _{PHL}	A to Y (Figures 3 and 4)	C _L = 50 pF		_	6.4	11.5	-	13.0	_	16.0	
	,	C _L = 15 pF	4.5 to 5.5	_	3.5	5.5	-	6.5	_	8.5	
		C _L = 50 pF		_	4.5	7.5	-	8.5	_	10.5	
t _{PZL} ,	Output Enable	C _L = 15 pF	3.0 to 3.6	-	4.5	8.0	-	9.5	_	11.5	ns
t _{PZH}	Time, OE to Y (Figures 3 and 4)	C _L = 50 pF		_	6.4	11.5	-	13.0	_	15.0	
	,	C _L = 15 pF	4.5 to 5.5	-	3.5	5.1	-	6.0	_	8.5	
		C _L = 50 pF		_	4.5	7.1	-	8.0	_	10.5	
t _{PLZ} ,	Output Disable	C _L = 15 pF	3.0 to 3.6	-	6.5	9.7	-	11.5	_	14.5	ns
t _{PHZ}	Time, OE to Y (Figures 3 and 4)	C _L = 50 pF		_	8.0	13.2	-	15.0	_	18.0	
	,	C _L = 15 pF	4.5 to 5.5	_	4.8	6.8	-	8.0	_	10.0	
		C _L = 50 pF		_	7.0	8.8	-	10.0	_	12.0	
C _{IN}	Input Capacitance			_	4.0	10	-	10	_	10	pF
C _{OUT}	Output Capacitance	Output in High Impedance State		-	6.0	I	-	-	-	-	pF

		Typical @ 25°C, V _{CC} = 5.0 V	
C _{PD}	Power Dissipation Capacitance (Note 5)	8.0	pF

^{5.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.



 R_L, Ω C_L , pF **Position** See AC Characteristics Table t_{PLH} / t_{PHL} Open Χ 1 k t_{PLZ} / t_{PZL} V_{CC} GND 1 k t_{PHZ} / t_{PZH}

X = Don't Care

Test

Switch

 $\ensuremath{C_L}$ includes probe and jig capacitance R_T is Z_{OUT} of pulse generator (typically 50 Ω) f = 1 MHz

Figure 3. Test Circuit

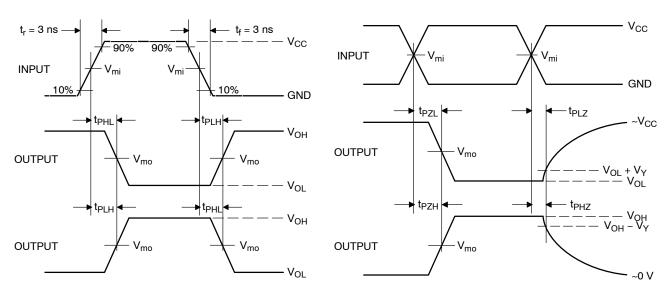


Figure 4. Switching Waveforms

		V _m		
V _{CC} , V	V _{mi} , V	t _{PLH} , t _{PHL}	t_{PZL} , t_{PLZ} , t_{PZH} , t_{PHZ}	V _Y , V
3.0 to 3.6	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.3
4.5 to 5.5	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.3

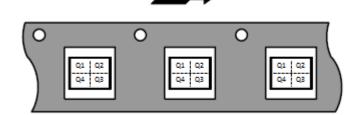
ORDERING INFORMATION

Device	Packages	Specific Device Code	Pin 1 Orientation (See below)	Shipping [†]
M74VHC1G125DFT1G	SC-88A	W0	Q2	3000 / Tape & Reel
M74VHC1G125DFT2G	SC-88A	W0	Q4	3000 / Tape & Reel
NLVVHC1G125DFT1G*	SC-88A	W0	Q2	3000 / Tape & Reel
M74VHC1GT125DF1G	SC-88A	W1	Q2	3000 / Tape & Reel
M74VHC1GT125DF2G	SC-88A	W1	Q4	3000 / Tape & Reel
NLVVHC1GT125DF1G*	SC-88A	W1	Q2	3000 / Tape & Reel
NLVVHC1GT125DF2G*	SC-88A	W1	Q4	3000 / Tape & Reel
MC74VHC1G125DBVT1G	SC-74A	W0	Q4	3000 / Tape & Reel
MC74VHC1GT125DBVT1G	SC-74A	W1	Q4	3000 / Tape & Reel
M74VHC1G125DTT1G	TSOP-5	W0	Q4	3000 / Tape & Reel
M74VHC1GT125DT1G	TSOP-5	W1	Q4	3000 / Tape & Reel
NLVVHC1GT125DT1G*	TSOP-5	W1R	Q4	3000 / Tape & Reel
MC74VHC1G125XV5T2G (In Development)	SOT-553	TBD	Q4	4000 / Tape & Reel
MC74VHC1GT125XV5T2G (In Development)	SOT-553	TBD	Q4	4000 / Tape & Reel
MC74VHC1G125P5T5G	SOT-953	Т	Q2	8000 / Tape & Reel
MC74VHC1GT125P5T5G (In Development)	SOT-953	TBD	Q2	8000 / Tape & Reel
MC74VHC1G125MU1TCG (In Development)	UDFN6, 1.45 x 1.0, 0.5P	TBD	Q4	3000 / Tape & Reel
MC74VHC1GT125MU1TCG	UDFN6, 1.45 x 1.0, 0.5P	D	Q4	3000 / Tape & Reel
MC74VHC1GT125MU2TCG	UDFN6, 1.2 x 1.0, 0.4P	7	Q4	3000 / Tape & Reel
MC74VHC1G125MU3TCG (In Development)	UDFN6, 1.0 x 1.0, 0.35P	TBD	Q4	3000 / Tape & Reel
MC74VHC1GT125MU3TCG	UDFN6, 1.0 x 1.0, 0.35P	L	Q4	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Pin 1 Orientation in Tape and Reel

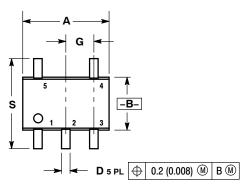
Direction of Feed

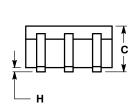


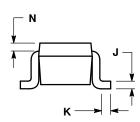
^{*}NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

PACKAGE DIMENSIONS

SC-88A (SC-70-5/SOT-353) CASE 419A-02 ISSUE L



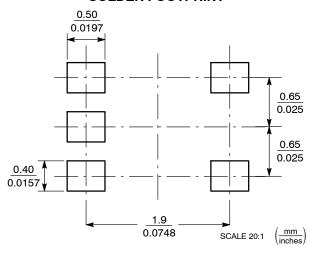




- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. 419A-01 OBSOLETE. NEW STANDARD 419A-02.
 4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.071	0.087	1.80	2.20	
В	0.045	0.053	1.15	1.35	
C	0.031	0.043	0.80	1.10	
D	0.004	0.012	0.10	0.30	
G	0.026 BSC		0.65 BSC		
Н		0.004		0.10	
J	0.004	0.010	0.10	0.25	
K	0.004	0.012	0.10	0.30	
N	0.008 REF		0.20 REF		
S	0.079	0.087	2.00	2.20	

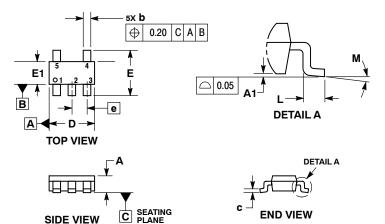
SOLDER FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

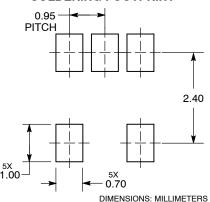
SC-74A CASE 318BQ **ISSUE B**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
 4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE.

	MILLIMETERS		
DIM	MIN	MAX	
Α	0.90	1.10	
A1	0.01	0.10	
b	0.25	0.50	
C	0.10	0.26	
D	2.85	3.15	
E	2.50	3.00	
E1	1.35	1.65	
е	0.95 BSC		
L	0.20	0.60	
М	0 °	10°	

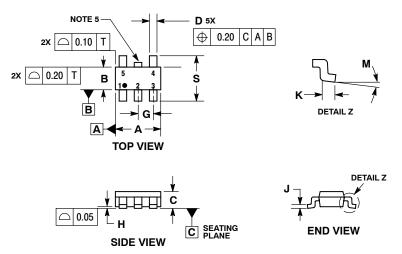
RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

TSOP-5 CASE 483-02 **ISSUE M**



- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

 2. CONTROLLING DIMENSION: MILLIMETERS.

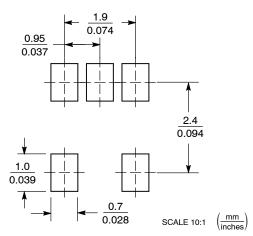
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

 4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSION A.

 5. OPTIONAL CONSTRUCTION: AN ADDITIONAL
 - OPTIONAL CONSTRUCTION: AN ADDITIONAL TRIMMED LEAD IS ALLOWED IN THIS LOCATION. TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2 FROM BODY.

	MILLIMETERS		
DIM	MIN	MAX	
Α	2.85	3.15	
В	1.35	1.65	
С	0.90	1.10	
D	0.25	0.50	
G	0.95 BSC		
Н	0.01	0.10	
J	0.10	0.26	
K	0.20	0.60	
М	0 °	10°	
S	2.50	3.00	

SOLDERING FOOTPRINT*

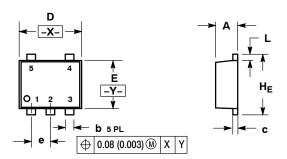


*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SOT-553, 5 LEAD

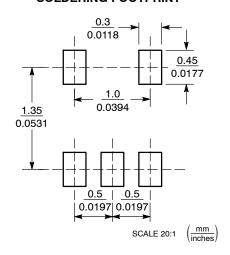
CASE 463B ISSUE C



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETERS
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH
 THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM
 THICKNESS OF BASE MATERIAL.

	MILLIMETERS		INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.50	0.55	0.60	0.020	0.022	0.024
b	0.17	0.22	0.27	0.007	0.009	0.011
С	0.08	0.13	0.18	0.003	0.005	0.007
D	1.55	1.60	1.65	0.061	0.063	0.065
E	1.15	1.20	1.25	0.045	0.047	0.049
е		0.50 BSC			0.020 BSC	
L	0.10	0.20	0.30	0.004	0.008	0.012
HE	1.55	1.60	1.65	0.061	0.063	0.065

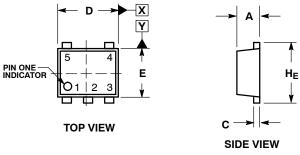
SOLDERING FOOTPRINT*

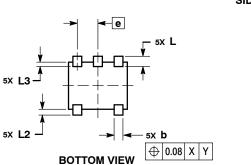


*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SOT-953 CASE 527AE **ISSUE E**

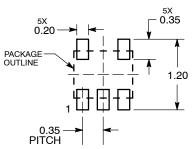




- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE
- MINIMUM THICKNESS OF THE BASE MATERIAL. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			
DIM	MIN	NOM	MAX	
Α	0.34	0.37	0.40	
b	0.10	0.15	0.20	
С	0.07	0.12	0.17	
D	0.95	1.00	1.05	
Е	0.75	0.80	0.85	
е	0.35 BSC			
HE	0.95	1.00	1.05	
L	0.175 REF			
L2	0.05	0.10	0.15	
L3			0.15	

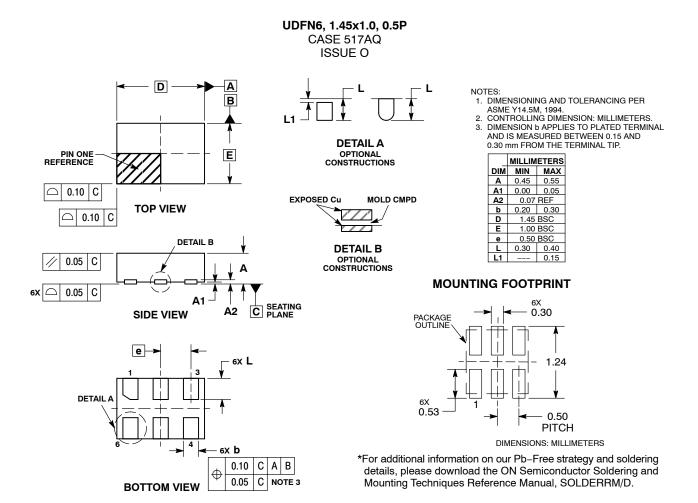
SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

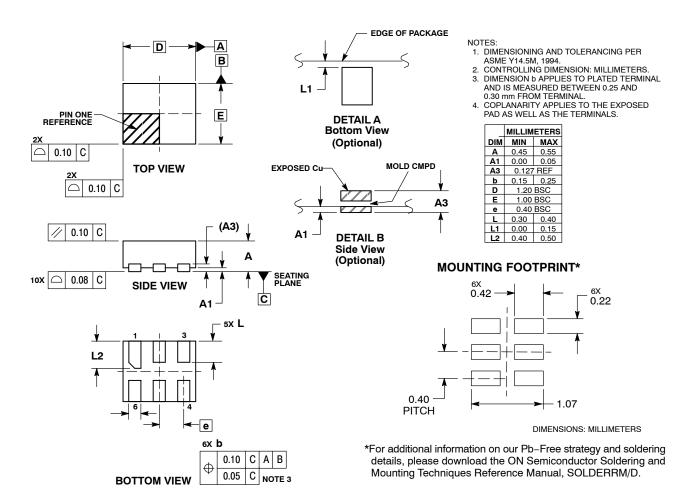
^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

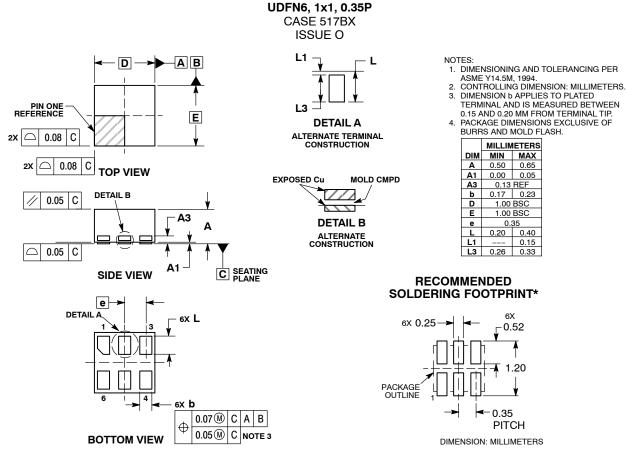


PACKAGE DIMENSIONS

UDFN6, 1.2x1.0, 0.4P CASE 517AA-01 ISSUE D



PACKAGE DIMENSIONS



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